	2020	01217001.2	D		PCN	l Da	te:	Mar 18,	2021	
Title: Qual	ification of RFA	AB as an additional Fab site option				r se	lect LB	C7 device	s	
Customer Cont		PCN Manac		· · ·	Dep			Quality S		
				Estima			ple	- ,	Date provided at	
Proposed 1 st Sh	np Date:	Jul 25, 202	.1	Availat			•	sample r		
Change Type:										
Assembly Si	te		bly Process		[nbly Mate		
Design		Electrical Specification							ecification	
Test Site		Packing/Shipping/Labeling						Process		
Wafer Bump		Wafer Bump Material					Wafer Bump Process Wafer Fab Process			
🛛 🛛 Wafer Fab S	ite		Fab Materia			\boxtimes	Wafer	r Fab Proc	cess	
			umber chan							
Description of (Changes		PCN Deta	IIIS						
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	Current Site			A	ddit	iona	al Site	I Site		
Current Fal	Process	Wafe	Add	itional	F	Process		Wafer		
Current Fab		Diamet	or Fat	s Site				Diame	tor	
Site FFAB	LBC7	Diamet 200mn	n R	Site FAB		LBO		Diame 300m		
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Automotive Qualification Summary

(As per AEC-Q100 and JEDEC Guidelines)

UCC27524A1QDGNRQ1 and UCC27524AQDRQ1 FFAB to RFAB

Approve Date 22-October-2020

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

	Data Displayed as: Number of fota / fotal sample size / fotal failed											
Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: UCC27524A1QDGNRQ1	Qual Device: UCC27524AQDRQ1	Process QBS Reference TPS2543QRTE	Product QB S Reference UCC27524AQDRQ1	Package QBS Reference PGA308AQDGSRQ1	Package QBS Reference UCC27524
Test Group A – Accelerated Environment Stress Tests												
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	96 Hours	-	-	3/231/0	1/77/0	3/231/0	3/231/0
AC	A3	JEDEC JESD22-A102	3	77	Autoclave 121C	96 Hours	-	-	3/231/0	1/77/0	3/231/0	-
uHAST	A3	JEDEC JESD22-A102	3	77	unBiased HAST, 130C/85%RH	96 Hours	-	1/77/0	-	-	-	3/231/0
тс	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, - 65/150C	500 Cycles	-	1/77/0	3/231/0	1/77/0	3/231/0	3/231/0
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle	1000 Cycles	N/A	N/A	N/A	N/A	N/A	N/A
HTSL	A6	JEDEC JESD22-A103	1	45	High Temp. Storage Bake, 175C	500 Hours	-	1/45/0	1/45/0	1/45/0	1/45/0	3/231/0
Test Group B – Accelerated Lifetime Simulation Tests												
HTOL	81	JEDEC JESD22-A108	3	77	Life Test, 150C	408 Hours	-	-	3/231/0		3/231/0	-
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 140C	480 Hours	-	-	-	2/154/0	-	-
ELFR	B 2	AEC Q100-008	3	800	Early Life Failure Rate, 125C	48 Hours	-	-	3/2640/0	1/800/0	3/2400/0	-
EDR	B3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A	N/A	N/A	N/A	3/231/0	-
Fest Group	C – Pa	ackage Assembly I	Integrit	y Tests								
WBS	C1	AEC Q100-001	1	30	Bond Shear (Cpk>1.67)	Wires	1/30/0	1/30/0	-	-	-	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Bond Pull (Cpk>1.67)	Wires	1/30/0	1/30/0	-	-	-	3/90/0
SD	C3	JEDEC JESD22-B102	1	15	Solderability (>95% Lead Coverage)	Pb & Pb-Free	-	-	1/15/0	-	-	-
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions (Cpk>1.67)	-	-	-	3/30/0	-	-	3/30/0

Т	Test Group D – Die Fabrication Reliability Tests												
	EM	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
	TDDB	D2	JESD35	-	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
	HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
	NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
	SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Т	Test Group E – Electrical Verification Tests												
	HBM	E2	AEC Q100-002	1	3	ESD - HBM	4000 V	1/3/0	1/3/0	-	-	-	
	CDM	E3	AEC Q100-011	1	3	ESD - CDM	1000 V	1/3/0	1/3/0	-	-	-	-
	LU	E4	AEC Q100-004	1	6	Latch-up	(Per AEC Q100-004)	1/6/0	1/6/0	1/6/0	-	-	-
	ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, Hot, & Cold Test	3/90/0	3/90/0	3/90/0	3/90/0	-	-

Qual Device UCC27524A1QDGNRQ1 is qualified at LEVEL2-260C Qual Device UCC27524AQDRQ1 is qualified at LEVEL1-260C A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable. Performed for IHB, Biased HAST, AC, BHAST, AC, BHAST, IC & PTC sample Ambient Operating Temperature by Automotive Grade Level: Grade 0 (or E): -40°C to +150°C Grade 2 (or T): -40°C to +155°C Grade 3 (or 1): -40°C to +85°C E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold : HTOL, ED Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room : AC/uHAST Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

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